

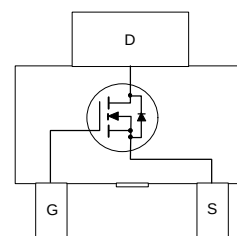
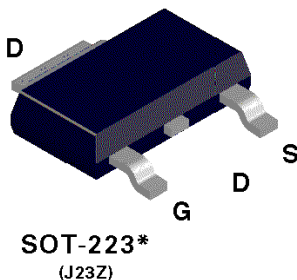
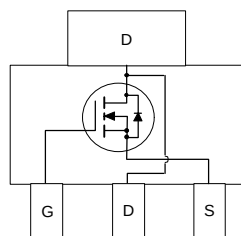
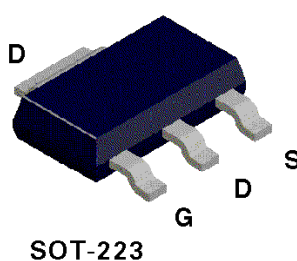
FDT459N N-Channel Enhancement Mode Field Effect Transistor

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance, provide superior switching performance. These products are well suited to low voltage, low current applications such as notebook computer power management, battery powered circuits, and DC motor control.

Features

- 6.5 A, 30 V. $R_{DS(ON)} = 0.035\Omega @ V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 0.055 \Omega @ V_{GS} = 4.5 \text{ V}$.
- High density cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability in a widely used surface mount package.



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDT459N	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage - Continuous	± 20	V
I_D	Maximum Drain Current - Continuous (Note 1a)	6.5	A
	- Pulsed	20	
P_D	Maximum Power Dissipation (Note 1a)	3	W
	(Note 1b)	1.3	
	(Note 1c)	1.1	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	42	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	12	$^\circ\text{C/W}$

* Order option J23Z for cropped center drain lead.

Electrical Characteristics (T_A = 25 °C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
--------	-----------	------------	-----	-----	-----	-------

OFF CHARACTERISTICS

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	I _D = 250 μA, Referenced to 25 °C		33		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V T _J = 55°C			1 10	μA
I _{GSSF}	Gate - Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA

ON CHARACTERISTICS (Note 2)

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1	1.6	2	V
ΔV _{GS(th)} /ΔT _J	Gate Threshold Voltage Temp. Coefficient	I _D = 250 μA, Referenced to 25 °C		-4.2		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 6.5 A T _J = 125°C V _{GS} = 4.5 V, I _D = 5.5 A		0.031 0.044 0.046	0.035 0.06 0.055	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	20			A
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 6.5 A		16		S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 15 V, V _{GS} = 0 V, f = 1.0 MHz		365		pF
C _{oss}	Output Capacitance			210		pF
C _{rss}	Reverse Transfer Capacitance			70		pF

SWITCHING CHARACTERISTICS (Note 2)

t _{D(on)}	Turn - On Delay Time	V _{DD} = 15 V, I _D = 1 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		5.2	11	ns
t _r	Turn - On Rise Time			8.2	16	ns
t _{D(off)}	Turn - Off Delay Time			6	12	ns
t _f	Turn - Off Fall Time			16	26	ns
Q _g	Total Gate Charge	V _{DS} = 10 V, I _D = 6.5 A, V _{GS} = 10 V		12	17	nC
Q _{gs}	Gate-Source Charge			2.2		nC
Q _{gd}	Gate-Drain Charge			3		nC

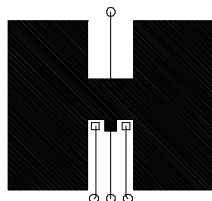
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I _S	Maximum Continuous Drain-Source Diode Forward Current				2.5	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.5 A (Note 2)		0.8	1.2	V

Notes:

1. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJA} is guaranteed by design while R_{θCA} is determined by the user's board design.

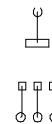
Typical R_{θJA} using the board layouts shown below on FR-4 PCB in a still air environment:



a. 42°C/W when mounted on a 1 in² pad of 2oz Cu.



b. 95°C/W when mounted on a 0.066 in² pad of 2oz Cu.



c. 110°C/W when mounted on a 0.00123 in² pad of 2oz Cu.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

Typical Electrical Characteristics

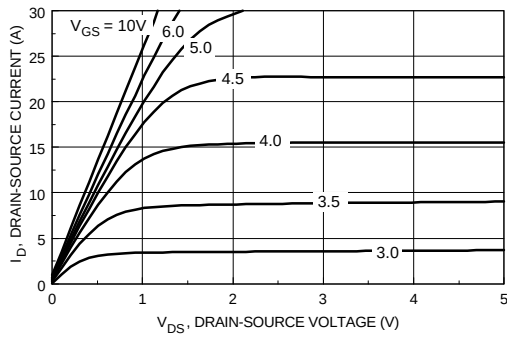


Figure 1. On-Region Characteristics.

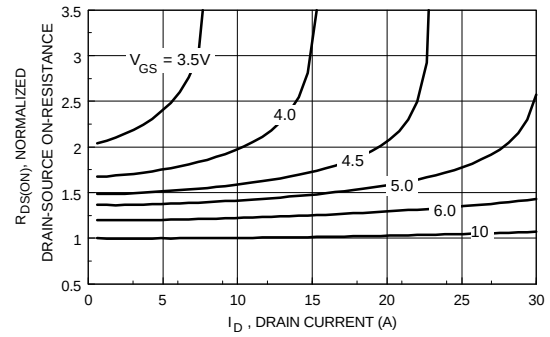


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

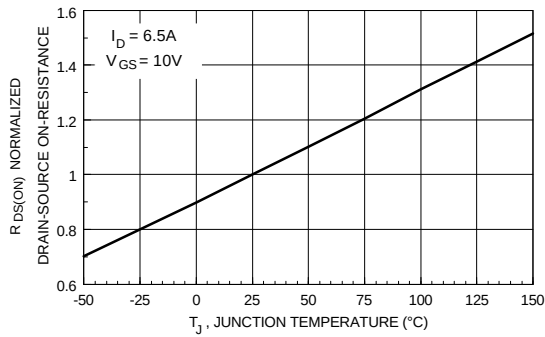


Figure 3. On-Resistance Variation with Temperature.

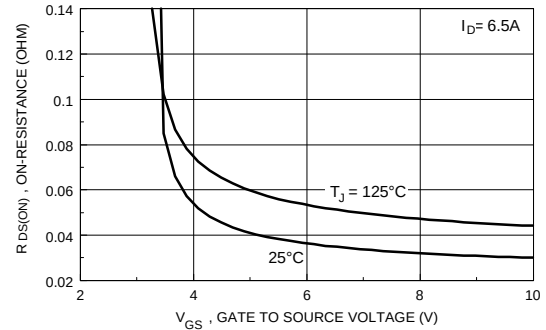


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

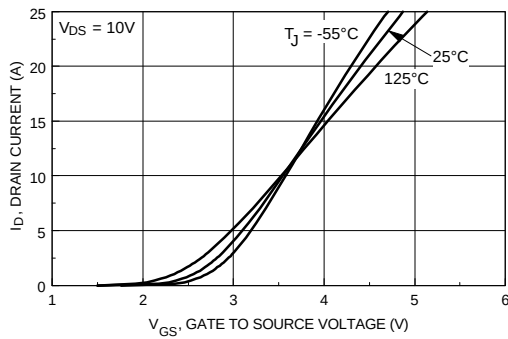


Figure 5. Transfer Characteristics.

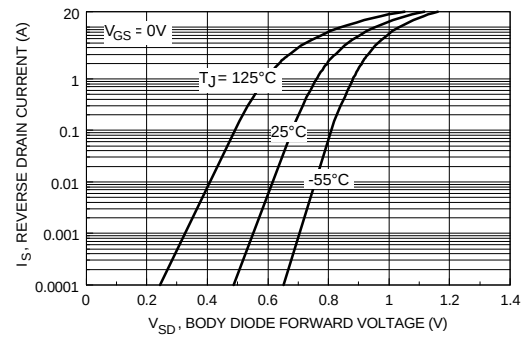


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics

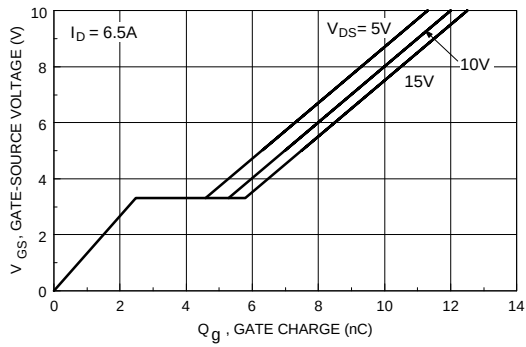


Figure 7. Gate Charge Characteristics.

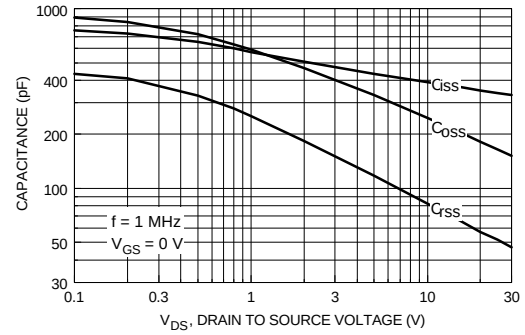


Figure 8. Capacitance Characteristics.

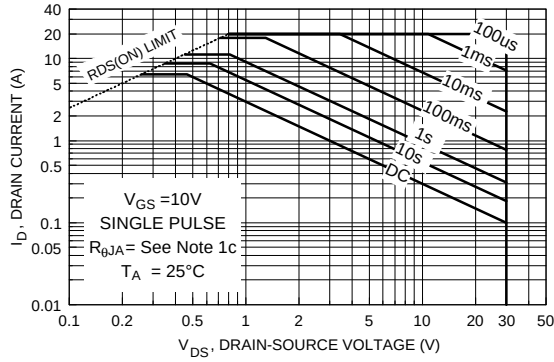


Figure 9. Maximum Safe Operating Area.

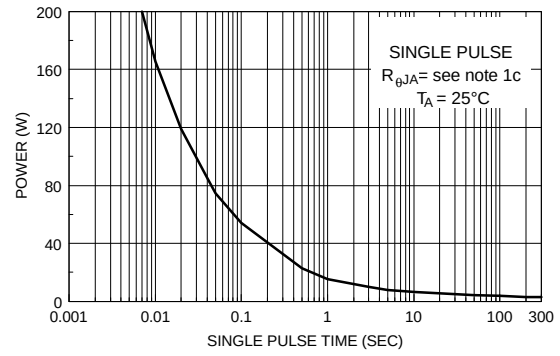


Figure 10. Single Pulse Maximum Power Dissipation.

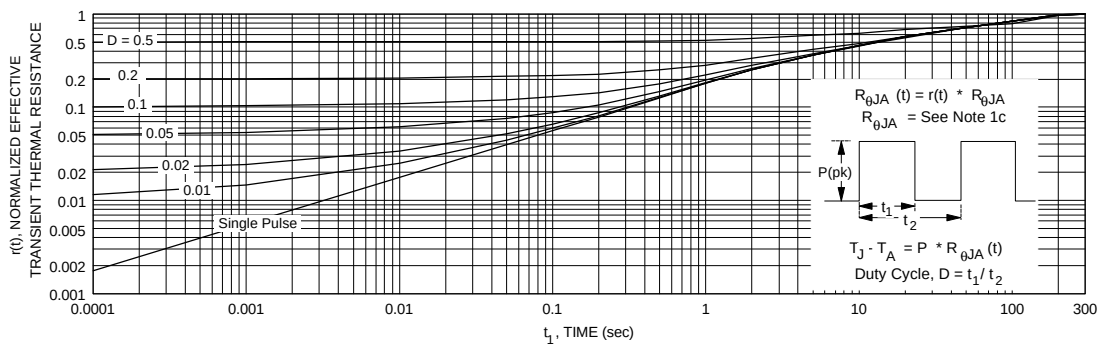


Figure 11. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c.
Transient thermal response will change depending on the circuit board design.

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^{Ex} TM	FAST [®]	OPTOLOGIC TM	SMART START TM	VCX TM
Bottomless TM	FAST ^r TM	OPTOPLANAR TM	STAR*POWER TM	
CoolFET TM	FRFET TM	PACMAN TM	Stealth TM	
CROSSVOLT TM	GlobalOptoisolator TM	POP TM	SuperSOT TM -3	
DenseTrench TM	GTO TM	Power247 TM	SuperSOT TM -6	
DOME TM	HiSeC TM	PowerTrench [®]	SuperSOT TM -8	
EcoSPARK TM	ISOPLANAR TM	QFET TM	SyncFET TM	
E ² CMOS TM	LittleFET TM	QS TM	TinyLogic TM	
EnSigna TM	MicroFET TM	QT Optoelectronics TM	TruTranslation TM	
FACT TM	MicroPak TM	Quiet Series TM	UHC TM	
FACT Quiet Series TM	MICROWIRE TM	SILENT SWITCHER [®]	UltraFET [®]	

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.